March 3, 2011

RFMD(R) Achieves Milestone in Commercialization of High-Performance Photovoltaic Cells

GREENSBORO, N.C., March 3, 2011 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced it has successfully achieved another significant performance milestone related to the commercialization of high-performance photovoltaic (PV) cells.

Specifically, RFMD has fabricated dual-junction PV cells that integrate gallium arsenide (GaAs) and indium gallium phosphide (InGaP) PV junctions using the Company's standard six-inch semiconductor equipment. The successful fabrication of the dual-junction PV cells clears the way for RFMD to develop triple-junction structures, with the ultimate goal of developing a commercially viable and high volume-capable compound semiconductor-based process for high-performance PV cells.

Bob Bruggeworth, president and CEO of RFMD, said, "RFMD is very pleased with the world-class performance of our dual-junction cells. With this achievement, RFMD is demonstrating we possess the critical technologies to produce a low-cost PV product with competitive solar cell conversion efficiency, supported by the quality, reliability, and volumes that characterize the cellular handset market."

In 2009, RFMD announced it had entered into a cooperative agreement with the U.S. Department of Energy's National Renewable Energy Laboratory (NREL) for the purpose of developing a production capable process technology for high-performance PV cells. NREL has decades of research experience and expertise in PV cell technology, and RFMD is a pioneer and industry leader in compound semiconductor manufacturing with a proven ability to commercialize new technologies.

The dual-junction achievement and associated performance characteristics are consistent with results achieved by NREL in their development of Inverted Metamorphic Multi-Junction (IMM) technology. NREL's technology has demonstrated one of the world's highest reported solar cell conversion efficiencies, at 40.8 percent, and continued substantial improvements in efficiency are anticipated.

RFMD's dual-junction achievement was realized using the Company's existing manufacturing capabilities and robust supply chain, which are optimized for high volume, low cost, reliability and performance. The conversion efficiency achieved across RFMD's six-inch wafers was exceptionally uniform, enabling high device yields and tight distributions in CPV product performance.

RFMD's development efforts related to a compound semiconductor-based process for PV cells are broadly applicable across technologies, including IMM as well as conventional triple-junction Germanium-based CPV devices. RFMD anticipates multiple opportunities related to PV cells and is engaged with CPV system integrators and solar cell module manufacturers.

About NREL

NREL is the U.S. Department of Energy's primary national laboratory for renewable energy and energy efficiency research and development. NREL is operated for DOE by the Alliance for Sustainable Energy, LLC.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6436

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private

Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

CONTACT: Douglas DeLieto

VP of Investor Relations

RF Micro Devices

336-678-7088

Source: RF Micro Devices

News Provided by Acquire Media